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Kind regards,

Team Nexperia

NPN/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = open

Rev. 01 — 17 February 2005

Product data sheet

1. Product profile

1.1 General description

NPN/PNP resistor-equipped transistors.

Table I. Product overview	Table	1:	Product	overview
---------------------------	-------	----	---------	----------

Type number	Package	Package F		NPN/NPN	
	Philips	JEITA	complement	complement	
PEMD19	SOT666	-	PEMB19	PEMH19	
PUMD19	SOT363	SC-88	PUMB19	PUMH19	

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
lo	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ



006aaa269

NPN/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = open

2. Pinning information

Table 3:	Pinning					
Pin	Description	Simplified outline	Symbol			
1	GND (emitter) TR1					
2	input (base) TR1					
3	output (collector) TR2					
4	GND (emitter) TR2					
5	input (base) TR2					
6	output (collector) TR1	R1				
			1 2 3			

3. Ordering information

Table 4: Ordering information					
Type number Package					
	Name	Description	Version		
PEMD19	-	plastic surface mounted package; 6 leads	SOT666		
PUMD19	SC-88	plastic surface mounted package; 6 leads	SOT363		

4. Marking

Table 5: Marking codes	
Type number	Marking code [1]
PEMD19	6E
PUMD19	T4*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

NPN/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = open

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor v	with negative polar	ity		
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
lo	output current (DC)		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1] [2] _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2] _	300	mW

[1] Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Thermal characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
stor					
thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
SOT363		<u>[1]</u> -	-	625	K/W
SOT666		<u>[1]</u> <u>-</u>	-	625	K/W
e					
thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
SOT363		<u>[1]</u> -	-	416	K/W
SOT666		<u>[1]</u> <u>[2]</u> _	-	416	K/W
	Parameter stor thermal resistance from junction to ambient SOT363 SOT666 e thermal resistance from junction to ambient SOT363 SOT666	ParameterConditionsstorthermal resistance from junction to ambient $T_{amb} \le 25 \text{ °C}$ SOT363SOT666sotthermal resistance from junction to ambient $T_{amb} \le 25 \text{ °C}$ sotsotSOT363	ParameterConditionsMinstorthermal resistance from junction to ambient $T_{amb} \le 25 \ ^{\circ}C$ SOT363[1] - SOT666SOT666[1] [2] -thermal resistance from junction to ambient $T_{amb} \le 25 \ ^{\circ}C$ thermal resistance from junction to ambient $T_{amb} \le 25 \ ^{\circ}C$	ParameterConditionsMinTypstorthermal resistance from junction to ambient $T_{amb} \le 25 \ ^{\circ}C$.SOT363[1]SOT666[1] [2]thermal resistance from junction to ambient $T_{amb} \le 25 \ ^{\circ}C$.thermal resistance from junction to ambient $T_{amb} \le 25 \ ^{\circ}C$.	ParameterConditionsMinTypMaxstorthermal resistance from junction to ambient $T_{amb} \le 25 \ ^{\circ}C$

[1] Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

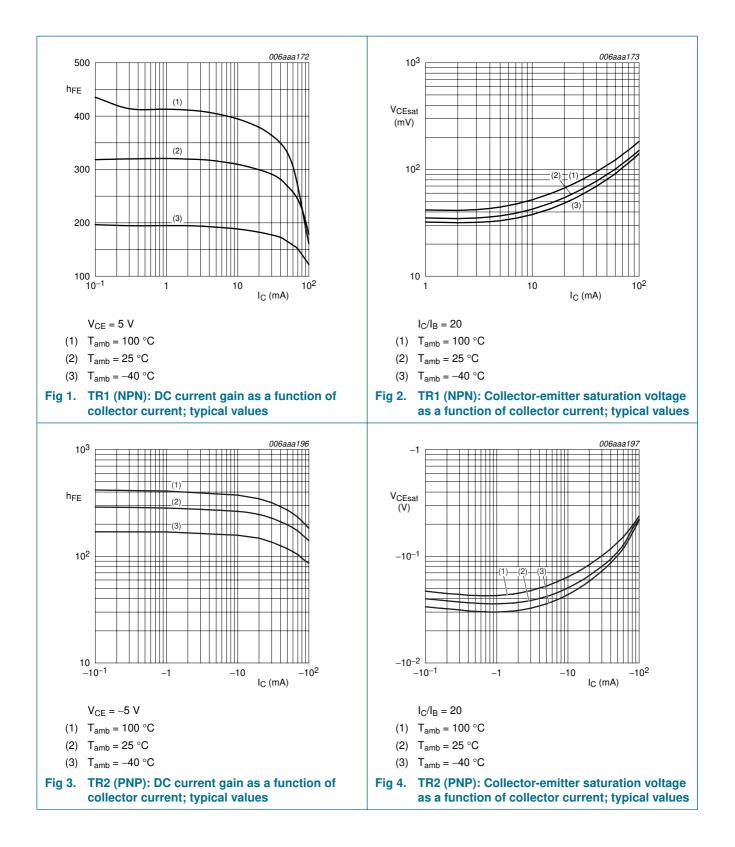
NPN/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = open

7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor; for the PNP transis	tor with negative polarity				
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	1	μA
		$\label{eq:VCE} \begin{array}{l} V_{CE}=30 \text{ V}; \text{ I}_{B}=0 \text{ A}; \\ T_{j}=150 \ ^{\circ}\text{C} \end{array}$	-	-	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 10 \text{ mA}; I_{B} = 0.5 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz} \end{array}$				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

PEMD19; PUMD19

NPN/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = open



PEMD19; PUMD19

NPN/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = open

8. Package outline

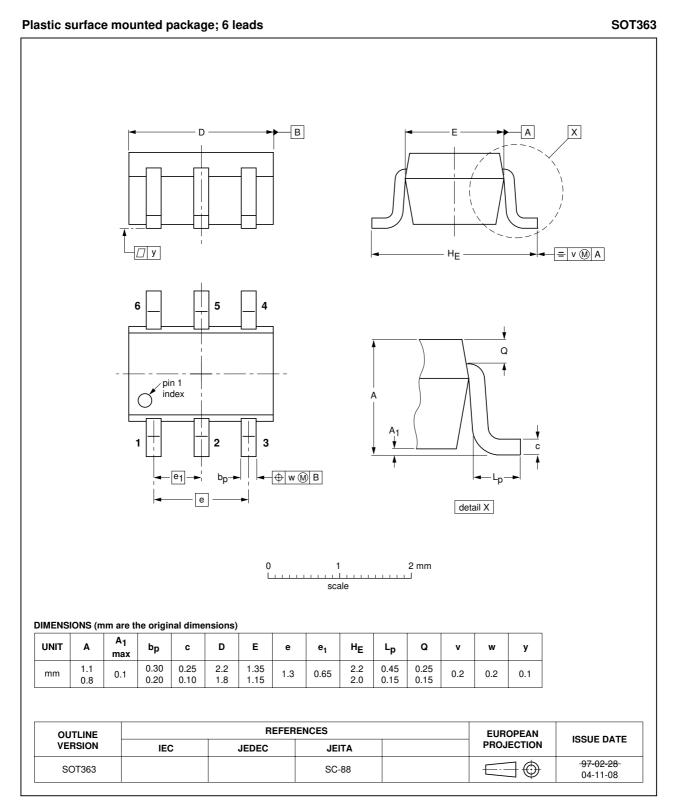


Fig 5. Package outline SOT363 (SC-88)

PEMD19; PUMD19

NPN/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = open

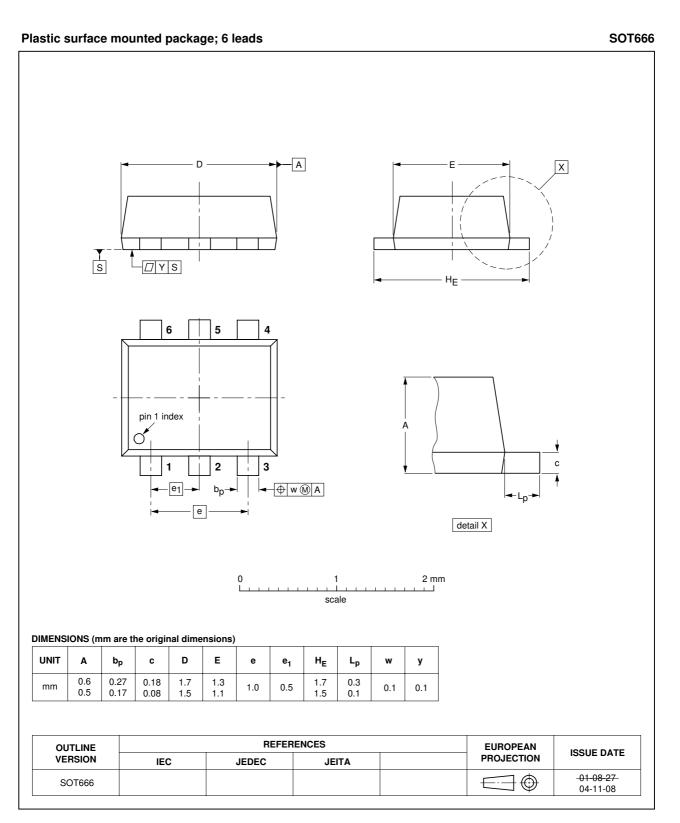


Fig 6. Package outline SOT666

9397 750 14408 Product data sheet NPN/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = open

9. Packing information

Table 9: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing of	quantity	
			3000	4000	10000
PEMD19	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
PUMD19	SOT363	4 mm pitch, 8 mm tape and reel; T1	2] -115	-	-135
PUMD19	SOT363	4 mm pitch, 8 mm tape and reel; T2	<u>-125</u>	-	-165

[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T2: reverse taping

NPN/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = open

10. Revision history

Table 10: Revision h	e 10: Revision history					
Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes	
PEMD19_PUMD19_1	20050217	Product data sheet	-	9397 750 14408	-	

NPN/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = open

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Level	Data sheet status [1]	Product status [2] [3]	Definition
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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PEMD19; PUMD19

NPN/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = open

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Date of release: 17 February 2005 Document number: 9397 750 14408

Published in The Netherlands